

Semiconductor and printed electronics processing technologies

Wet Chemical Processes

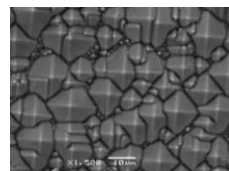
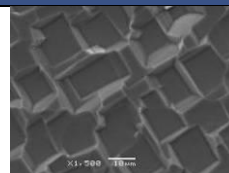
Description:

- Batch wet-bench processes



Processes:

- Saw damage etching of silicon substrate in KOH solution
- Selective alkaline etching of silicon substrate leading to a pyramid structure – textured surface
- Sequential wafer cleaning - in bath of aqueous solutions NH_4OH , H_2O_2 , HF , HCl
- Wafer drying in spin rinse dryer and in hot air oven with forced circulation



Class purity: ISO Class 4

Capacity: 100 substrates per hour

Handling: batches, PP and PFA carriers for 25 wafers - 5 and 6 inch size

High Temperature Processes

Description:

Equipments for high temperature processes used in production of solar cells and other semiconductor devices are installed in clean room.

Processes:

- POCl_3 and BBr_3 diffusion
- LPCVD a PECVD deposition of dielectric layers
- Thermal oxidation (optionally)

Class purity: ISO Class 3

Deposition of Dielectric Layers - PECVD

- Single tube furnace
- Quartz tube 300mm in diameter
- Vacuum system with dry pump Adixen
- Advanced process control system for control and monitoring of process parameters via touch terminal
- Substrates are loaded on a graphite boat moved into quartz reactor
- Vacuum-tight doors are part of the loading system
- Multisource gas board
- RF power generator – 450kHz




Process:

- PECVD one-side deposition of thin dielectric layers - SiN_x , SiO_x , AlO_x
- Processing temperature up to 450°C

Substrate: crystalline silicon wafer, formats 125x125 mm and 156x156 mm

Capacity: 108 substrates per hour

Producer: SVCS Process Innovation s.r.o. (CZ)

Three Tubes Furnace for High Temperature Processes – Diffusion and LPCVD	
<ul style="list-style-type: none"> • Quartz tube with diameter of 300 mm • Advanced control system controlling all process parameters via touch terminals • Substrates loaded on quartz boats are moved on silicon carbide paddle into individual quartz reactors • Vacuum system with dry pump Adixen for LPCVD • Liquid sources for diffusion processes 	<p>Process tube A:</p> <ul style="list-style-type: none"> ■ LPCVD deposition of dielectric layers, Si_3N_4 a SiO_2, at temperatures up to 800°C (position L) <p>Sample: crystalline silicon wafers, quartz boats for wafers 125x125mm and 156x156mm</p> <p>Capacity: 200 substrates per hour</p> <p>Process tube B:</p> <ul style="list-style-type: none"> ■ Creating a PN junction by POCl_3 diffusion at atmospheric pressure and at temperatures up to 950°C (position M) <p>Sample: crystalline silicon wafers, quartz boats for wafers 125x125mm and 156x156mm</p> <p>Capacity: 300 substrates per hour</p> <p>Process tube C:</p> <ul style="list-style-type: none"> ■ Creating a PN junction by BBr_3 diffusion at atmospheric pressure and at temperatures up to 1050°C (position H) <p>Substrate: crystalline silicon wafers, quartz boats for wafers 125x125mm and 156x156mm</p> <p>Capacity: 200 substrates per hour</p> <p>Producer: SVCS Process Innovation s.r.o. (CZ)</p>
Three Tubes Diffusion Furnace with Automatic Loading System	
<ul style="list-style-type: none"> • Advanced control system controlling all process parameters via touch terminals • Soft landing loading system • Liquid sources for diffusion processes 	<p>Process:</p> <ul style="list-style-type: none"> ■ Creating a PN junction by POCl_3 diffusion at atmospheric pressure and at temperatures up to 950°C <p>Substrate: crystalline silicon wafer, format up to $156 \times 156 \text{ mm}^2$</p> <p>Capacity: 600 substrates per hour</p> <p>Producer: Centrotherm (D)</p>

Thin Film Technology

Deposition of Thin Layers by Magnetron Sputtering

Sputtering system:

- 0,75m³ chamber with rotating holder
- Two positions for targets
- Huettinger DC sources with SPARKLE pulse unit
- PinnaclePlus pulse source-frequency up to 350 kHz
- Rotary and turbomolecular pump PFEIFFER
- Manual loading/unloading



Processes:

- Deposition of metallic and dielectric thin layers
- Holder for flat substrates

Substrate: various substrates, format up to 125 x 125 mm²

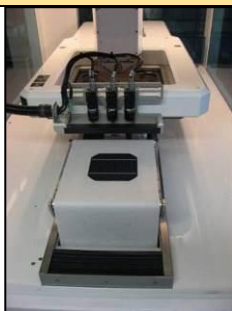
Capacity: 20 substrates per cycle

Thick Film Technology

Screen Printing

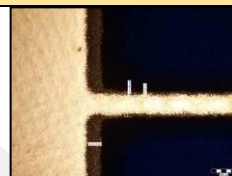
Equipment type A:

- Semiautomatic screen printer Baccini (IT)
- Squeegee movements by linear motors
- Vacuum printing table with protective paper
- Visualization system for very precision positioning print
- Manual loading



Processes:



- Printing of functional layers
- Printing area 200x200 mm
- Minimal printed line width - 40 μm
- Printing accuracy - 10 μm
- Designed for 12" screens with alu frames

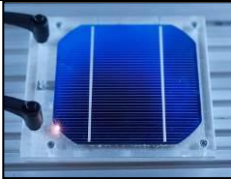
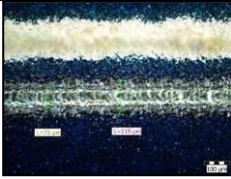


Substrate: crystalline silicon wafer, ceramic substrates, flexible substrates, ...


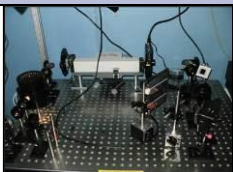

Capacity: 80 prints per hour


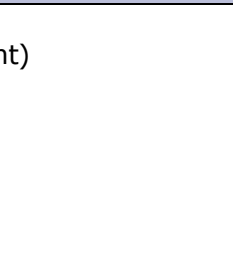
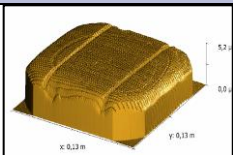


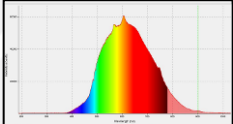
Number of units: 1

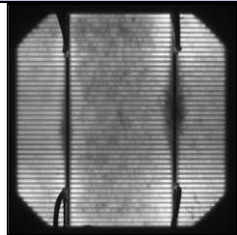



<p>Equipment type B:</p> <ul style="list-style-type: none"> • Automatic screen printer Baccini • Twin table system • Vacuum printing table with protective paper • Visualization system for very precision positioning print • Possible manipulation with substrates by walking beam • Squeegee movements by linear motors 	<p>Processes:</p> <ul style="list-style-type: none"> • Printing of functional layers • Printing area 200x200 mm • Designed for 12" screens with alu frames <p>Substrate: crystalline silicon wafer, ceramic substrates, flexible substrates, ...</p> <p>Capacity: 1.00 prints per hour Number of units: 3</p>
<p>Drying of Thick Film Pastes</p>	
<ul style="list-style-type: none"> • Dryer produced by Baccini (IT) • Substrates loaded on metal plates moved by side chains 	<p>Process:</p> <ul style="list-style-type: none"> • Drying of metallic and other functional pastes <p>Substrate: crystalline silicon wafers, ceramic and glass substrates</p> <p>Capacity: 1.000 substrates per hour Number of units: 2</p>
<p>Annealing and Sintering of Thick Film Pastes</p>	
<p>Equipment A:</p> <p>□ Continuous belt IR furnace</p> <p>SVCS</p> <ul style="list-style-type: none"> - contains seven individually controllable temperature zones, which are planted with linear halogen tubes - allows to adjust the dynamic temperature profile and the maximum temperature about 950°C - belt width 495 mm - manual loading/unloading 	<p>Process:</p> <ul style="list-style-type: none"> • Sintering of dried metallic and other functional pastes by annealing in the continuous belt IR furnace <p>Substrate: crystalline silicon wafers, ceramic and glass substrates</p> <p>Capacity: 500 substrates per hour</p>

Equipment B: <ul style="list-style-type: none"> • Continuous belt IR furnace Centrotherm • Contains five individually controllable temperature zones • Heated by linear halogen tubes • Adjustment of dynamic temperature profile with peak temperature 1.000°C • Wire conveyor belt with width of 600 mm • Machine handling system with output camera 	Process: <ul style="list-style-type: none"> • Sintering of dried metallic and functional pastes by annealing in the continuous belt IR furnace Substrate: crystalline silicon wafers, ceramic and glass substrates Capacity: 1.000 substrates per hour
Laser Technology	
Equipment: <ul style="list-style-type: none"> • The fiber-laser power of 20W and the wavelength of 1063 nm. Laser beam is deflected by galvo head, workspace size 180 x 180 mm² • Manual loading/unloading 	Processes: <ul style="list-style-type: none"> • Cutting, scribing and drilling of various substrates and solar cells • Creating microstructures (isolation of PN junction, scoring, piercing holes)  Substrate: crystalline silicon wafers, ceramic and glass substrates, format up to 156 x 156 mm ² Capacity: 100 substrates per hour
PV Modules Production	
Stringing	
Equipment: <ul style="list-style-type: none"> • Semiautomatic soldering head with step movement • Soldering by focused IR light 	Processes: <ul style="list-style-type: none"> • Soldering of interconnection ribbons on solar cells • Assembling of strings of crystalline silicon solar cells Substrate: crystalline silicon solar cells, format up to 156 x 156 mm ² Capacity: 12 strings per hour
Vacuum Lamination	
<ul style="list-style-type: none"> • Vacuum membrane laminator ICOLAM 38/24 produced by Meier Group • Chamber size: 4.130 x 2.780 x 170 mm • Electrically heated bottom plate 	Processes: <ul style="list-style-type: none"> • Lamination of PV modules Substrate: glass / back sheet modules Capacity: 8 modules per hour

DIAGNOSTIC TOOLS

Measurement of IV Curves of Solar Cells		
Equipment: <ul style="list-style-type: none"> • Sun simulators and equipment for measurement of IV curves • Two testers of solar cells • Sun simulators with Xelamp, continuous operation, intensity 1000W/sqm 		Measurement: <ul style="list-style-type: none"> • IV curves in the lighting solar simulator • Characteristics in bright or dark • Series resistance with IEC <p>Sample: solar cell, format up to 156 x156 mm²</p> <p>Capacity: 100 solar cells per hour</p>
Measurement of Quantum Efficiency		
Equipment: <ul style="list-style-type: none"> • Single grating monochromator • Halogen lamp for the probe and bias light beams • Optical components (mirrors, lenses and filters) from Edmund Optics • Chopper and lock-in technique 		Measurement: <ul style="list-style-type: none"> • Quantum efficiency of solar cells • Optical reflection of silicon substrates and solar cell structures in the spectral range 400-1200 nm <p>Sample: crystalline silicon solar cells, format up to 125 x 125 mm²</p>
Mapping of Minority Carriers Lifetime and Sheet Resistance		
Equipment: <ul style="list-style-type: none"> • WT2000 by Semilab • Mapping tool 		Measurement: <ul style="list-style-type: none"> • Mapping of lifetime of minority charge carriers by method MWPCD (Microwave Photoconductive Decay) • Mapping of sheet resistance • (SHR method, non-contact and non-destructive)

Measurement of Minority Carriers Lifetime		
Equipment: <ul style="list-style-type: none"> WCT120 by Sinton Consulting 		Measurement: <ul style="list-style-type: none"> Measurement of minority charge carriers by method QSSPC (Quasi Steady State PhotoConductivity) Measurement Suns-Voc Dependence of the generated open circuit voltage on illumination for the generation of pseudo V-A characteristics and fitting of diode characteristics of solar cells and parallel resistance Sample: solar cell, crystalline silicon wafer
LBIC		
Equipment: <ul style="list-style-type: none"> LBIC (Light Beam Induced Current) 		Measurement: <ul style="list-style-type: none"> Mapping of the current response of the solar cells in the local monochromatic light irradiation 
Measurement of Layer Resistance		
Equipment: <ul style="list-style-type: none"> Four-probe scanner 		Measurement: <ul style="list-style-type: none"> Coarse mapping of N+/ P+ layer resistance by four-probe method
Measurement of Spectroscopic Analysis		
Equipment: <ul style="list-style-type: none"> Spectra Suite Spectrometer 		Measurement: <ul style="list-style-type: none"> Absorbance, reflectance and emission, as well as absolute irradiance, color and chemical concentration 

Electroluminescence Imaging		
Equipment: <ul style="list-style-type: none"> • High resolution CCD camera 	Measurement: <ul style="list-style-type: none"> • Electroluminescence images of solar cells and PV modules 	
Optical Microscopy		
Equipment: <ul style="list-style-type: none"> • Optical microscope 		Measurement: <ul style="list-style-type: none"> • Microscope with digital camera and software for capturing of images with great depth of field (Deep-focus) 
Measurement of Surface Tension		
Equipment: <ul style="list-style-type: none"> • Apparatus for measuring the contact angle by Advex Instruments 		Measurement: <ul style="list-style-type: none"> • Measuring of the contact angle and evaluation of surface tension 